## Abstract

An object of this invention is to provide a method for making a junction which is simple in the process, high in the throughput, and can make a shallow junction with high accuracy. After the suitable state of a substrate surface adapted to the wavelength of an electromagnetic wave to be applied has been formed, the electromagnetic wave is applied to electrically activate impurities so that the excited energy is effectively absorbed within the impurity thin film, thereby effectively making a shallow junction.

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